



IRLIZ14GPBF Information



For Reference Only

Part Number IRLIZ14GPBF
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 60V 8A TO220FP**Package**TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRLIZ14GPBF Specifications

Manufacturer Part Number IRLIZ14GPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) E 20 Rds On (Max) E 20 Rds On (Max) E 20 Mounting Type Through Hole Supplier Device Package TO-220-3 Full Pack, Isolated Tab		
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Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 27W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
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FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 27W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case To-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	4V, 5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 27W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±10VFET Feature-Power Dissipation (Max)27W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 4.8A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	8.4nC @ 5V
FET Feature - Power Dissipation (Max) 27W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 4.8A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±10V
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Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	27W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	200 mOhm @ 4.8A, 5V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

IRLIZ14GPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLIZ14GPBF Payment Methods



















IRLIZ14GPBF Shipping Methods













If you have any question about IRLIZ14GPBF, please do not hesitate to contact us!

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